

RJK0451DPB

40V, 35A, 7.0mΩ max.

Silicon N Channel Power MOS FET
Power Switching

R07DS0073EJ0200

Rev.2.00

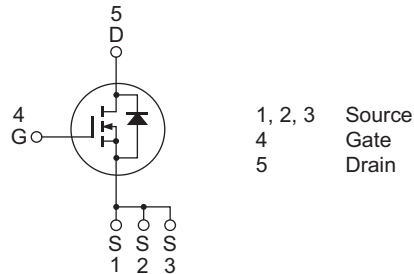
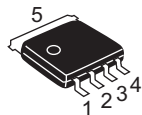
Apr 09, 2013

Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance
 $R_{DS(on)} = 5.5 \text{ m}\Omega$ typ. (at $V_{GS} = 10 \text{ V}$)
- Pb-free
- Halogen-free

Outline

RENESAS Package code: PTZZ0005DA-A
(Package name: LFPAK)



Application

- Switching Mode Power Supply

Absolute Maximum Ratings

($T_a = 25^\circ\text{C}$)

| Item | Symbol | Ratings | Unit |
|--|----------------------------------|-------------|---------------------------|
| Drain to source voltage | V_{DSS} | 40 | V |
| Gate to source voltage | V_{GSS} | ± 20 | V |
| Drain current | I_D | 35 | A |
| Drain peak current | $I_{D(pulse)}$ ^{Note 1} | 140 | A |
| Body-drain diode reverse drain current | I_{DR} | 35 | A |
| Avalanche current | I_{AP} ^{Note 2} | 17.5 | A |
| Avalanche energy | E_{AS} ^{Note 2} | 24.5 | mJ |
| Channel dissipation | P_{ch} ^{Note 3} | 45 | W |
| Channel to Case Thermal Resistance | θ_{ch-C} | 2.78 | $^\circ\text{C}/\text{W}$ |
| Channel temperature | T_{ch} | 150 | $^\circ\text{C}$ |
| Storage temperature | T_{stg} | -55 to +150 | $^\circ\text{C}$ |

- Notes: 1. $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$
 2. Value at $T_{ch} = 25^\circ\text{C}$, $R_g \geq 50 \Omega$
 3. $T_c = 25^\circ\text{C}$

This product is for the low voltage drive ($\leq 10\text{V}$).
 If the driving voltage is over 10 V under normal conditions, please use the product for high gate to source cutoff voltage ($V_{GS(off)}$) which characteristics has been improved.

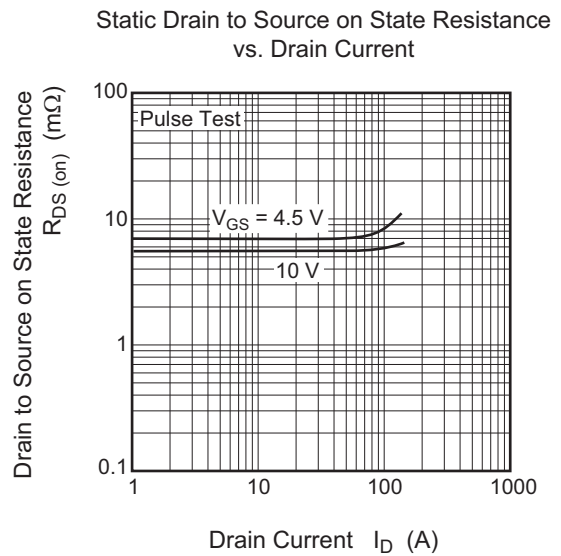
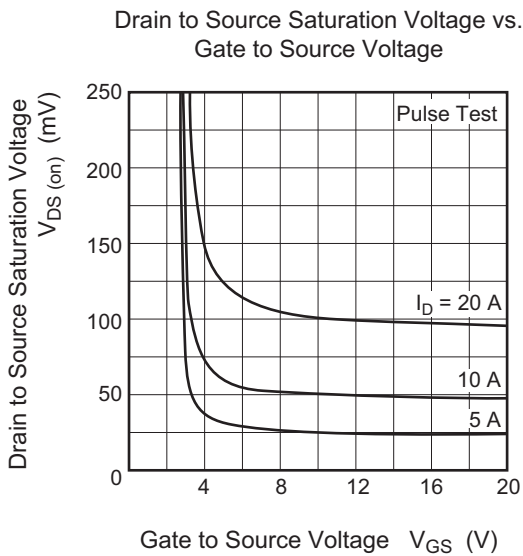
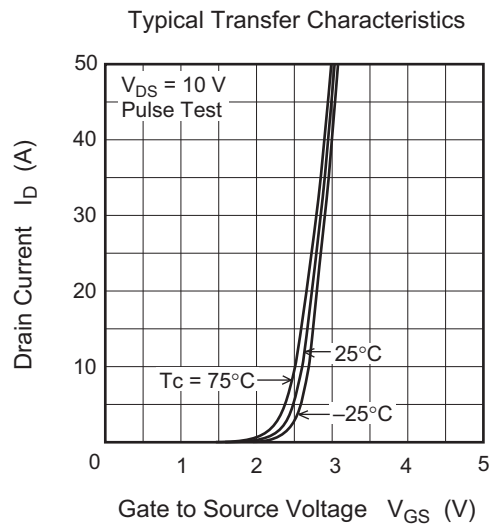
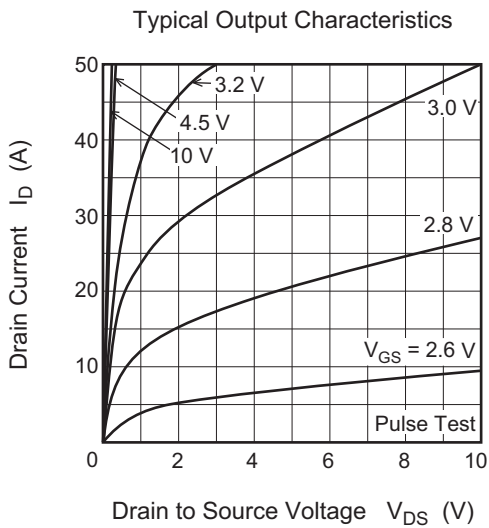
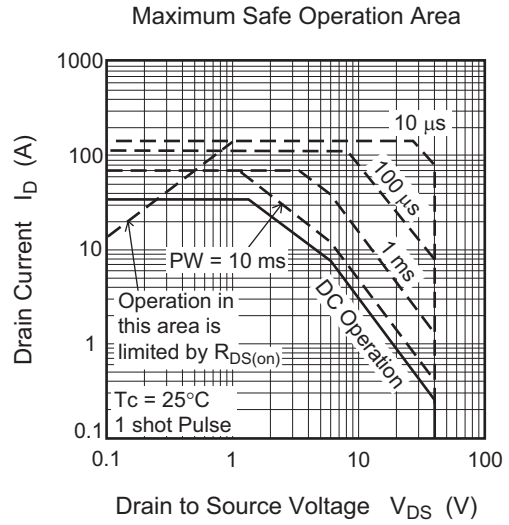
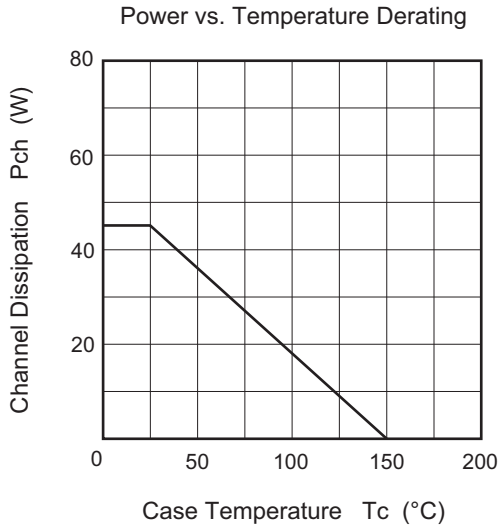
Electrical Characteristics

(Ta = 25°C)

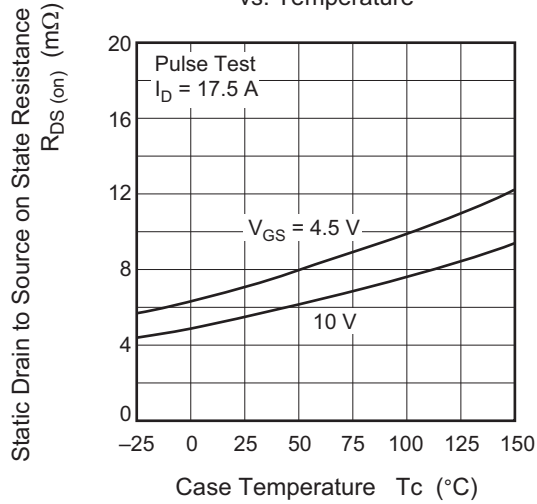
| Item | Symbol | Min | Typ | Max | Unit | Test Conditions |
|--|---------------|-----|------|-----------|------------------|---|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 40 | — | — | V | $I_D = 10 \text{ mA}$, $V_{GS} = 0 \text{ V}$ |
| Gate to source leak current | I_{GSS} | — | — | ± 0.1 | μA | $V_{GS} = \pm 20 \text{ V}$, $V_{DS} = 0 \text{ V}$ |
| Zero gate voltage drain current | I_{DSS} | — | — | 1 | μA | $V_{DS} = 40 \text{ V}$, $V_{GS} = 0 \text{ V}$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 1.2 | — | 2.5 | V | $V_{DS} = 10 \text{ V}$, $I_D = 1 \text{ mA}$ |
| Static drain to source on state resistance | $R_{DS(on)}$ | — | 5.5 | 7.0 | $\text{m}\Omega$ | $I_D = 17.5 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4} |
| | $R_{DS(on)}$ | — | 7.0 | 9.6 | $\text{m}\Omega$ | $I_D = 17.5 \text{ A}$, $V_{GS} = 4.5 \text{ V}$ ^{Note4} |
| Forward transfer admittance | $ y_{fs} $ | — | 47 | — | S | $I_D = 17.5 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4} |
| Input capacitance | C_{iss} | — | 2010 | — | pF | $V_{DS} = 10 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$ |
| Output capacitance | C_{oss} | — | 330 | — | pF | |
| Reverse transfer capacitance | C_{rss} | — | 140 | — | pF | |
| Gate Resistance | R_g | — | 0.7 | — | Ω | |
| Total gate charge | Q_g | — | 14 | — | nC | $V_{DD} = 10 \text{ V}$, $V_{GS} = 4.5 \text{ V}$, $I_D = 35 \text{ A}$ |
| Gate to source charge | Q_{gs} | — | 7.0 | — | nC | |
| Gate to drain charge | Q_{gd} | — | 3.0 | — | nC | |
| Turn-on delay time | $t_{d(on)}$ | — | 13 | — | ns | $V_{GS} = 10 \text{ V}$, $I_D = 17.5 \text{ A}$, $V_{DD} \cong 10 \text{ V}$, $R_L = 0.57 \Omega$, $R_g = 4.7 \Omega$ |
| Rise time | t_r | — | 4.8 | — | ns | |
| Turn-off delay time | $t_{d(off)}$ | — | 48 | — | ns | |
| Fall time | t_f | — | 6.0 | — | ns | |
| Body-drain diode forward voltage | V_{DF} | — | 0.83 | 1.1 | V | $I_F = 35 \text{ A}$, $V_{GS} = 0 \text{ V}$ ^{Note4} |
| Body-drain diode reverse recovery time | t_{rr} | — | 28 | — | ns | $I_F = 35 \text{ A}$, $V_{GS} = 0 \text{ V}$ $di_F/dt = 100 \text{ A}/\mu\text{s}$ |

Notes: 4. Pulse test

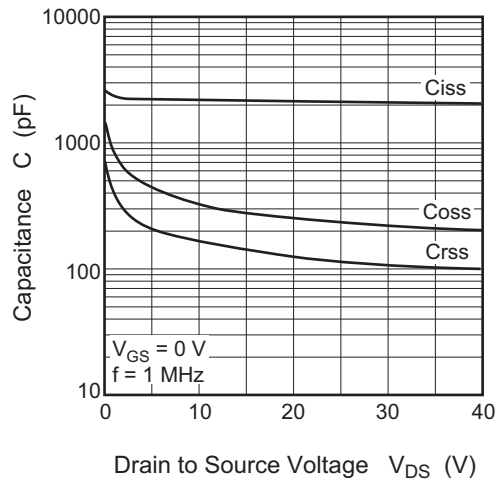
Main Characteristics



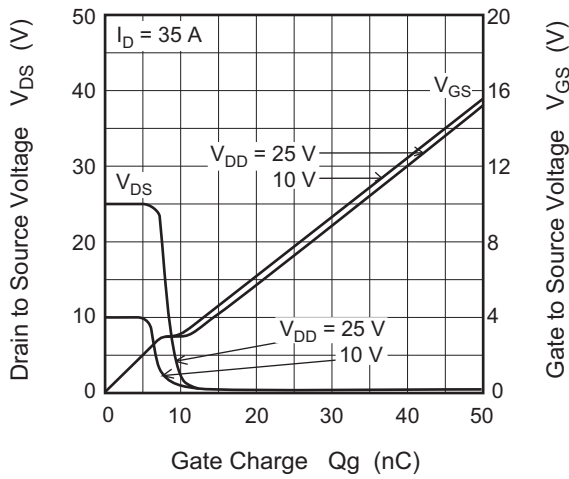
Static Drain to Source on State Resistance vs. Temperature



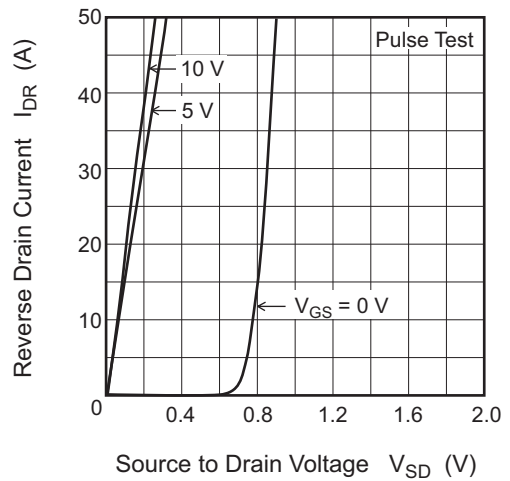
Typical Capacitance vs. Drain to Source Voltage



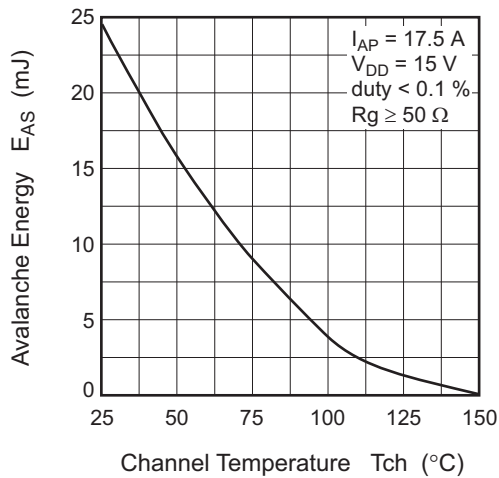
Dynamic Input Characteristics



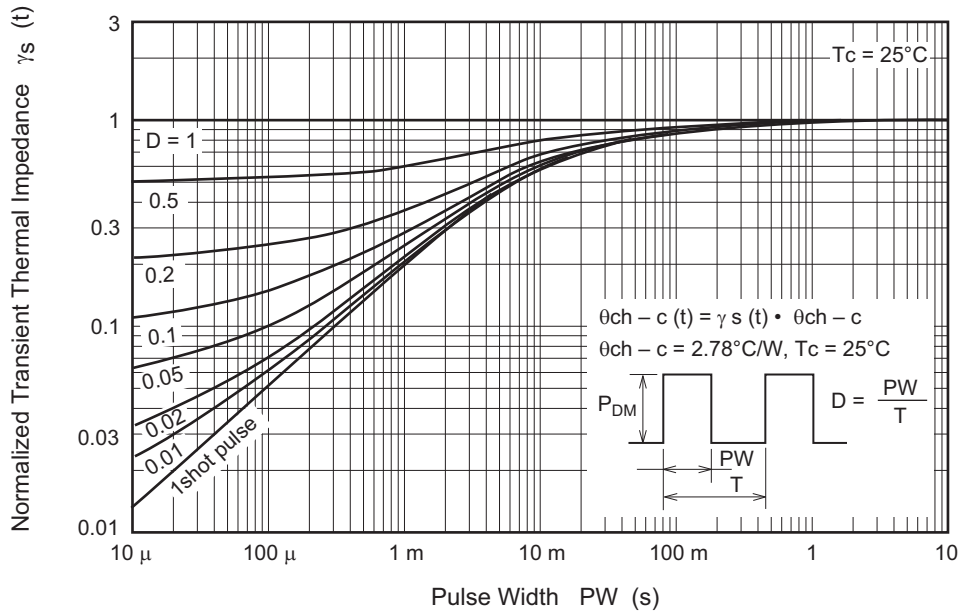
Reverse Drain Current vs. Source to Drain Voltage



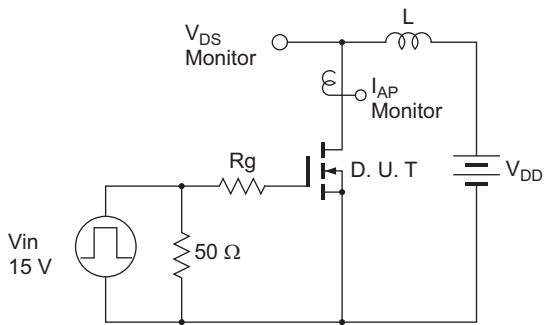
Maximum Avalanche Energy vs. Channel Temperature Derating



Normalized Transient Thermal Impedance vs. Pulse Width

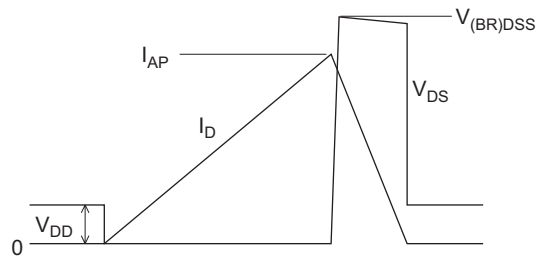


Avalanche Test Circuit

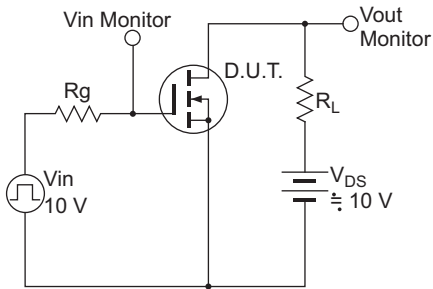


Avalanche Waveform

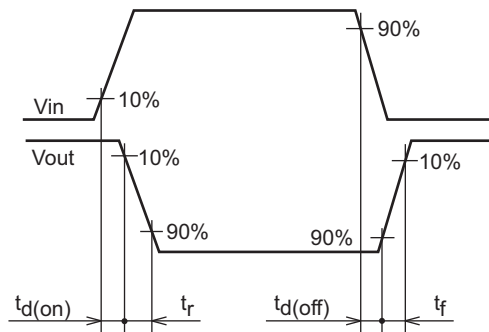
$$E_{AS} = \frac{1}{2} L \cdot I_{AP}^2 \cdot \frac{V_{DSS}}{V_{DSS} - V_{DD}}$$



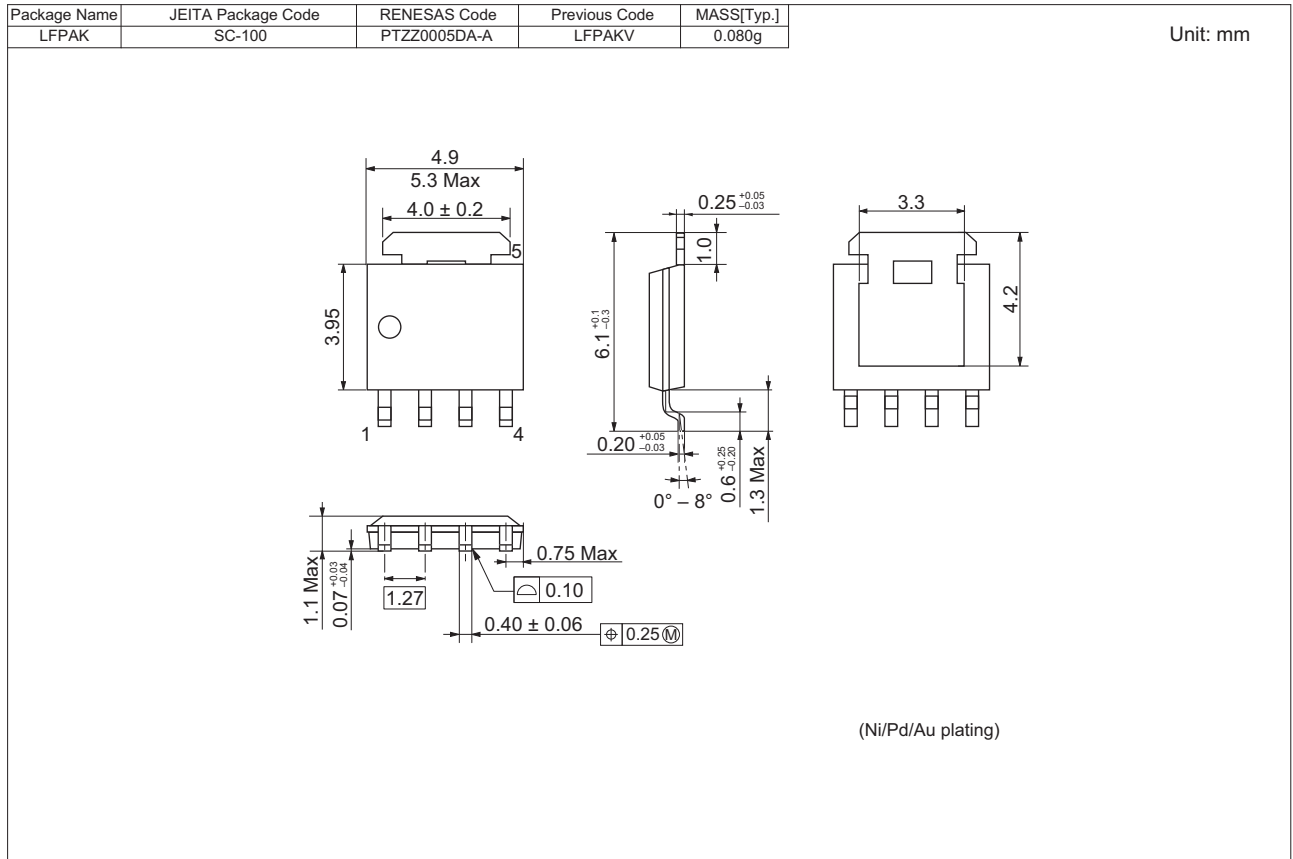
Switching Time Test Circuit



Switching Time Waveform



Package Dimensions



Ordering Information

| Part No. | Quantity | Shipping Container |
|------------------|----------|--------------------|
| RJK0451DPB-00-J5 | 2500 pcs | Taping |

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